Quad 2-Input AND Gate

The MC74VHCT08A is an advanced high speed CMOS 2-input AND gate fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The VHCT inputs are compatible with TTL levels. This device can be used as a level converter for interfacing 3.3 V to 5.0 V, because it has full 5.0 V CMOS level output swings.

The VHCT08A input structures provide protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. The output structures also provide protection when $V_{CC} = 0$ V. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7.0 V, allowing the interface of 5.0 V systems to 3.0 V systems.

Features

- High Speed: $t_{PD} = 4.3$ ns (Typ) at $V_{CC} = 5$ V
- Low Power Dissipation: $I_{CC} = 2 \mu A$ (Max) at $T_A = 25^{\circ}C$
- TTL-Compatible Inputs: $V_{IL} = 0.8 \text{ V}$; $V_{IH} = 2.0 \text{ V}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise: $V_{OLP} = 0.8 V (Max)$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: Human Body Model; > 2000 V, Machine Model; > 200 V
- Chip Complexity: 24 FETs or 6 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant

0	ON Semiconductor®					
http://onsemi.com MARKING						
Testeres 1	SOIC-14 D SUFFIX CASE 751A	DIAGRAMS				
1	TSSOP-14 DT SUFFIX CASE 948G	14RARARA VHCT 08A ALYW- 1UUUUUUU				
SOEIAJ-14 M SUFFIX CASE 965 14000000000000000000000000000000000000						
A = Assembly Location WL, L = Wafer Lot Y, YY = Year WW, W = Work Week G or • = Pb-Free Package (Note: Microdot may be in either location)						

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.



Figure 1. Logic Diagram



Figure 2. Pinout: 14-Lead Packages

FUNCTION TABLE

Inp	uts	Output
Α	В	Y
L	L	L
L	н	L
н	L	L
н	Н	Н

MAXIMUM RATINGS*

Rating	Symbol	Value	Unit
DC Supply Voltage	V _{CC}	-0.5 to +7.0	V
DC Input Voltage	V _{in}	-0.5 to +7.0	V
DC Output Voltage	V _{out}	–0.5 to V_CC +0.5	V
Input Diode Current	I _{IK}	-20	mA
Output Diode Current	I _{ОК}	±20	mA
DC Output Current, per Pin	l _{out}	±25	mA
DC Supply Current, V _{CC} and GND Pins	I _{CC}	±50	mA
Power Dissipation in Still Air, SOIC Packages† TSSOP Package†	PD	500 450	mW
Storage Temperature	T _{stg}	-65 to +150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND $\leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

* Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied.

†Derating – SOIC Packages: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Min	Max	Unit
DC Supply Voltage	V _{CC}	4.5	5.5	V
DC Input Voltage	V _{in}	0	5.5	V
DC Output Voltage	V _{out}	0	V _{CC}	V
Operating Temperature	T _A	-40	+ 125	°C
Input Rise and Fall Time V_{CC} = 5.0 V ± 0.5 V	t _r , t _f	0	20	ns/V

DC ELECTRICAL CHARACTERISTICS

			V _{CC}	T _A = 25°C		TA ≤	85°C	TA ≤ T	125°C		
Parameter	Test Conditions	Symbol	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
Minimum High-Level Input Voltage		V _{IH}	3.0 4.5 5.5	1.2 2.0 2.0			1.2 2.0 2.0		1.2 2.0 2.0		V
Maximum Low-Level Input Voltage		V _{IL}	3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8	V
	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \ \mu A$	V _{OH}	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		V
	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$		3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \ \mu A$	V _{OL}	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1	V
	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4 \text{ mA}$ $I_{OL} = 8 \text{ mA}$		3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	l _{IN}	0 to 5.5			±0.1		±1.0		±1.0	μΑ
Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	I _{CC}	5.5			2.0		20		40	μΑ
Quiescent Supply Current	Input: V _{IN} = 3.4 V	I _{CCT}	5.5			1.35		1.50		1.65	mA
Output Leakage Current	V _{OUT} = 5.5 V	I _{OPD}	0.0			0.5		5.0		10	μΑ

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ns}$)

			T _A = 25°C		$\mathbf{25^{\circ}C} \qquad \mathbf{T_{A}} \leq \mathbf{85^{\circ}C}$		T _A ≤ 125°C			
Characteristic	Test Conditions	Symbol	Min	Тур	Max	Min	Max	Max	Max	Unit
Maximum Propagation Delay, Input A or B to Y	$V_{CC} = 3.0 \pm 0.3 V \ C_L = 15 \ \text{pF} \\ C_L = 50 \ \text{pF}$	t _{PLH} , t _{PHL}		6.2 8.7	8.8 12.3		10.5 14.0		14.0 17.5	ns
	$V_{CC} = 5.0 \pm 0.5 V \ C_L = 15 \ pF \\ C_L = 50 \ pF$			4.3 5.8	5.9 7.9		7.0 9.0		9.0 11.0	
Maximum Input Capacitance		C _{in}		4	10		10		10	pF
		C _{PD}	Typical @ 25°C, V _{CC} = 5.0V							
Power Dissipation Capacitance	(Note 1)					20				pF

1. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}/4$ (per gate). C_{PD} is used to determine the no-load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}.7$

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns, $C_L = 50 pF$, $V_{CC} = 5.0$ V)

		T _A	= 25°C	
Characteristic	Symbol	Тур	Мах	Unit
Quiet Output Maximum Dynamic V _{OL}	V _{OLP}	0.3	0.8	V
Quiet Output Minimum Dynamic V _{OL}	V _{OLV}	-0.3	-0.8	V
Minimum High Level Dynamic Input Voltage	V _{IHD}		3.5	V
Maximum Low Level Dynamic Input Voltage	V _{ILD}		1.5	V



Figure 3. Switching Waveforms



*Includes all probe and jig capacitance



ORDERING INFORMATION

Device	Package	Shipping [†]
MC74VHCT08ADR2G	SOIC-14 (Pb-Free)	2500 Units / Tape & Reel
MC74VHCT08ADTR2G	TSSOP-14*	2500 Units / Tape &Reel
MC74VHCT08AMG	SOEIAJ-14 (Pb-Free)	50 Units / Rail
MC74VHCT08AMELG	SOEIAJ-14 (Pb-Free)	2000 Units / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*These packages are inherently Pb-Free.

PACKAGE DIMENSIONS

SOIC-14 **D SUFFIX** CASE 751A-03 **ISSUE J**



NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION. 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE. 5. DIMENSION D DOES NOT INCLUDE

PER SIDE. 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION CONDITION.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	8.55	8.75	0.337	0.344	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27 BSC		0.050	BSC	
J	0.19	0.25	0.008	0.009	
κ	0.10	0.25	0.004	0.009	
М	0 °	7 °	0 °	7 °	
Ρ	5.80	6.20	0.228	0.244	
R	0.25	0.50	0.010	0.019	

SOLDERING FOOTPRINT



PACKAGE DIMENSIONS



TSSOP-14

NOTES: 1. DIMENSIONING AND TOLERANCING PER

DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
CONTROLLING DIMENSION: MILLIMETER.
DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
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INTERLEAD FLASH OR PROTRUSION.
DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K

(0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL

DIMENSION AT MAXIMUM MATERIAL CONDITION. 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE - W-.

1	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026	BSC	
н	0.50	0.60	0.020	0.024	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
Κ	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	6.40 BSC		BSC	
М	0 °	8 °	0 °	8 °	
141	0	0	0	0	



PACKAGE DIMENSIONS

SOEIAJ-14 CASE 965-01 ISSUE B





DETAIL P





NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH

OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. 4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

THEFENENCE ONLY. 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.10	0.20	0.004	0.008
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050) BSC
H _E	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
М	0 °	10 °	0 °	10 °
Q ₁	0.70	0.90	0.028	0.035
Z		1.42		0.056

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